HCNR3906

30V N-Channel MOSFET

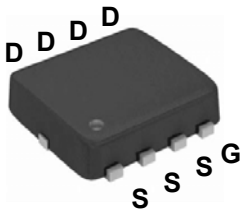
General Description

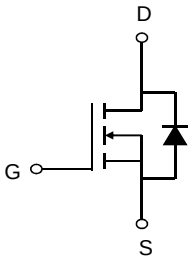
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

V_{DS}	30V
I_D (at V_{GS}=10V)	60A
$R_{DS(ON)}$ (at V_{GS}=10V)	4.8mΩ(Typ)
$R_{DS(ON)}$ (at V_{GS}=4.5V)	7.0mΩ(Typ)

PDFN3x3





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous	TC=25°C	I_D	60	A
	TC=100°C	I_D	38	A
Drain Current – Pulsed		I_{DM}	240	A
Maximum Power Dissipation		P_D	45	W
Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	℃

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance junction-case	$R_{\theta Jc}$		2.8	℃ /W
Thermal Resistance junction-to-Ambient	$R_{\theta JA}$		62	℃ /W

Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V,V_{GS}=0V			1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.0	1.6	2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=20A		4.8	6.0	mΩ
		V_{GS}=4.5V, I_D=10A		7.0	9.0	mΩ
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{DS}=25V,V_{GS}=0V, F=1.0MHz		1210		pF
C_{oss}	Output Capacitance			190		pF
C_{rss}	Reverse Transfer Capacitance			100		pF
SWITCHING PARAMETERS						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V V_{DS}=15V R_L=0.75Ω R_{GEN}=3Ω		7.3		nS
t_r	Turn-on Rise Time			14.5		nS
$t_{d(off)}$	Turn-Off Delay Time			35.8		nS
t_f	Turn-Off Fall Time			9.6		nS
Q_g	Total Gate Charge	V_{DS}=15V,I_D=4.5A, V_{GS}=4.5V		11		nC
Q_{gs}	Gate-Source Charge			1.85		nC
Q_{gd}	Gate-Drain Charge			6.8		nC
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_{SD}=1A		0.72	1.3	V
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz		2.5		Ω

Note：

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

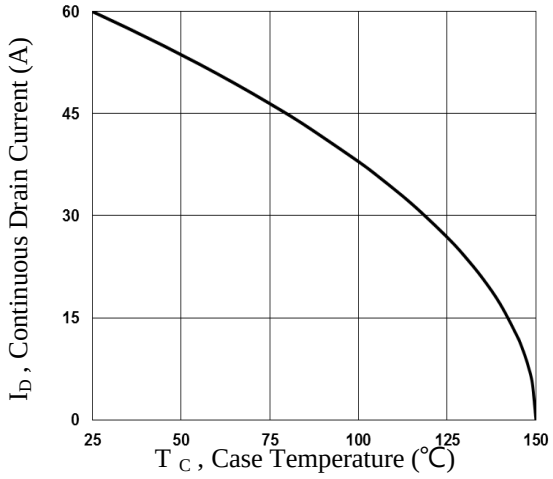


Fig.1 Continuous Drain Current vs. T_C

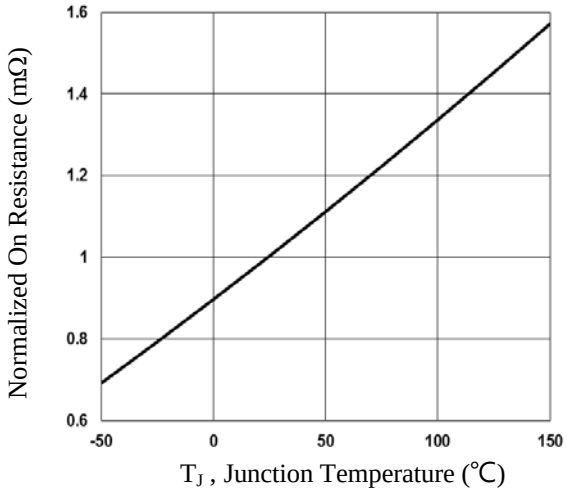


Fig.2 Normalized RDSON vs. T_J

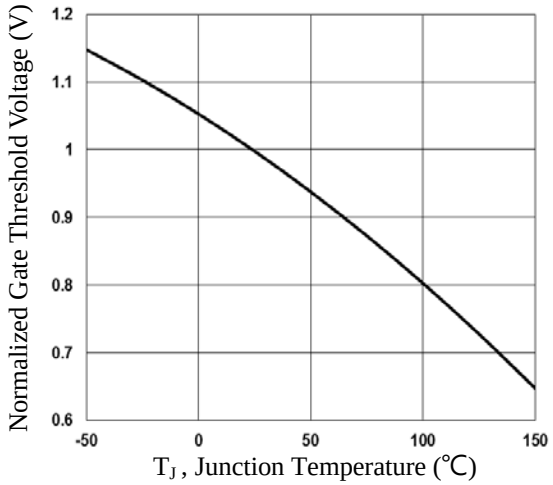


Fig.3 Normalized V_{th} vs. T_J

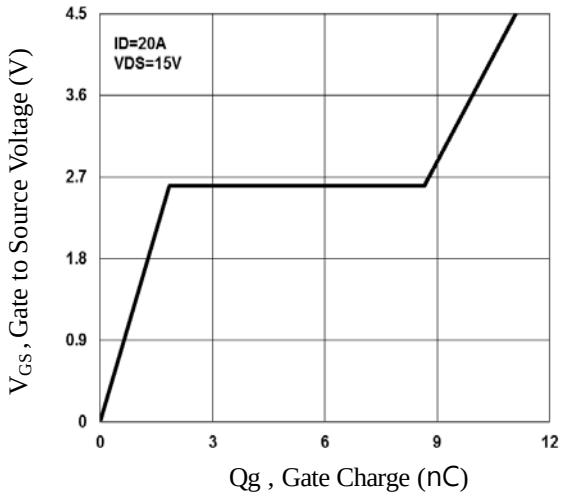


Fig.4 Gate Charge Waveform

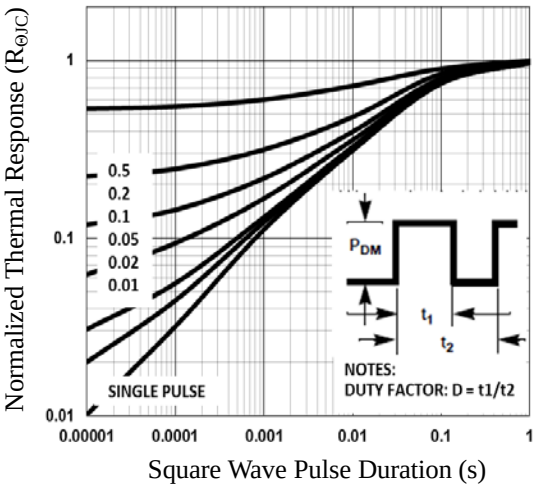


Fig.5 Normalized Transient Impedance

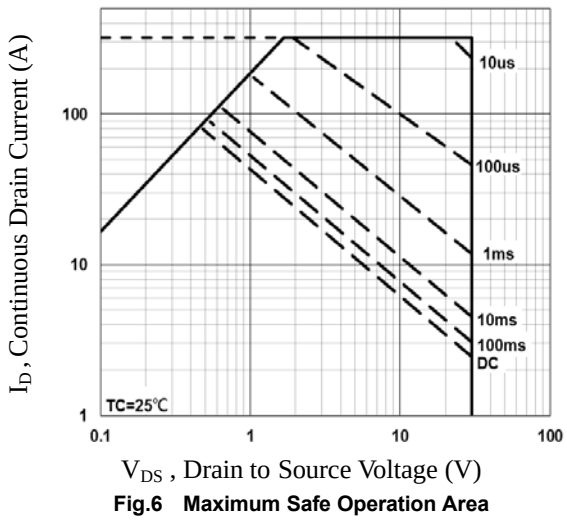


Fig.6 Maximum Safe Operation Area

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

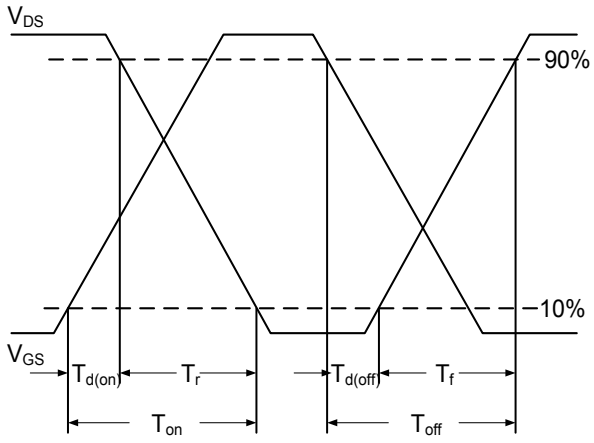


Fig.7 Switching Time Waveform

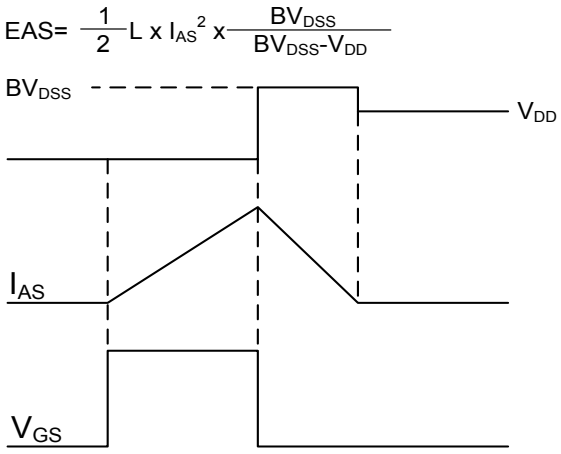
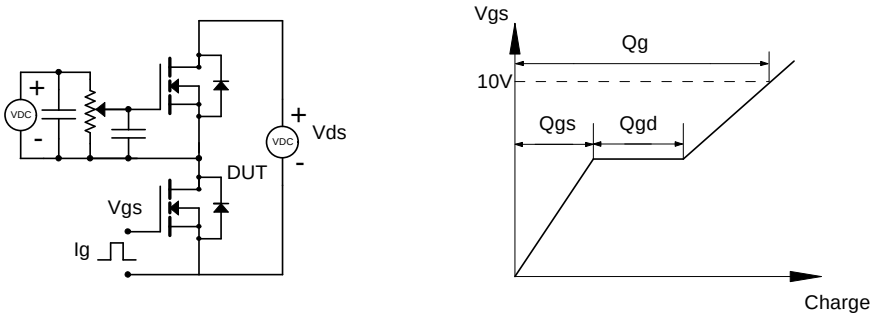
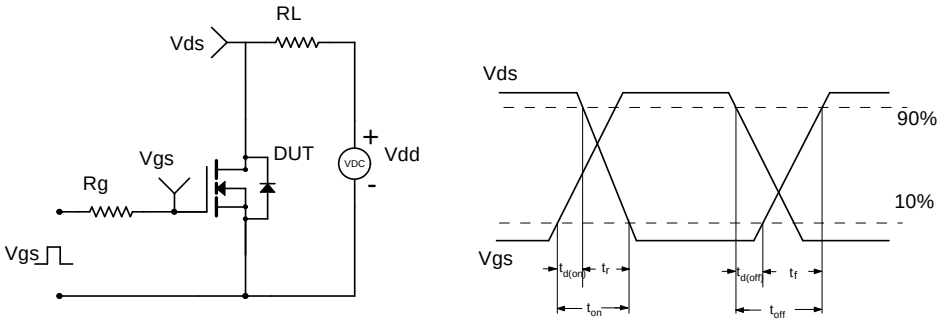


Fig.8 EAS Waveform

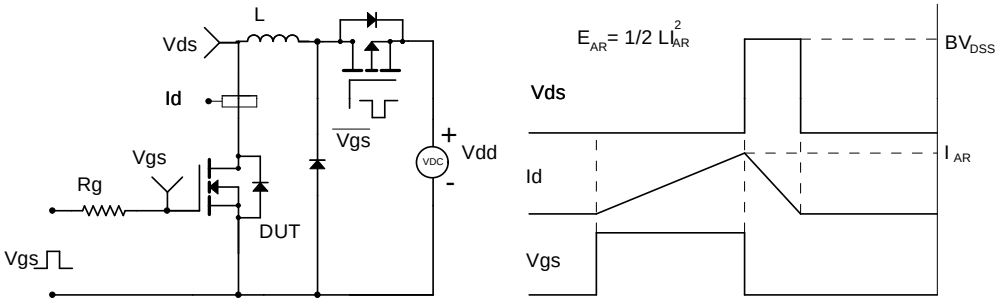
Gate Charge Test Circuit & Waveform



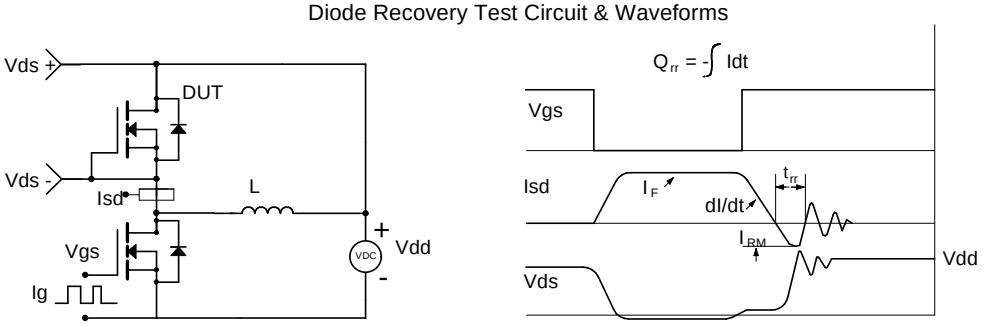
Resistive Switching Test Circuit & Waveforms



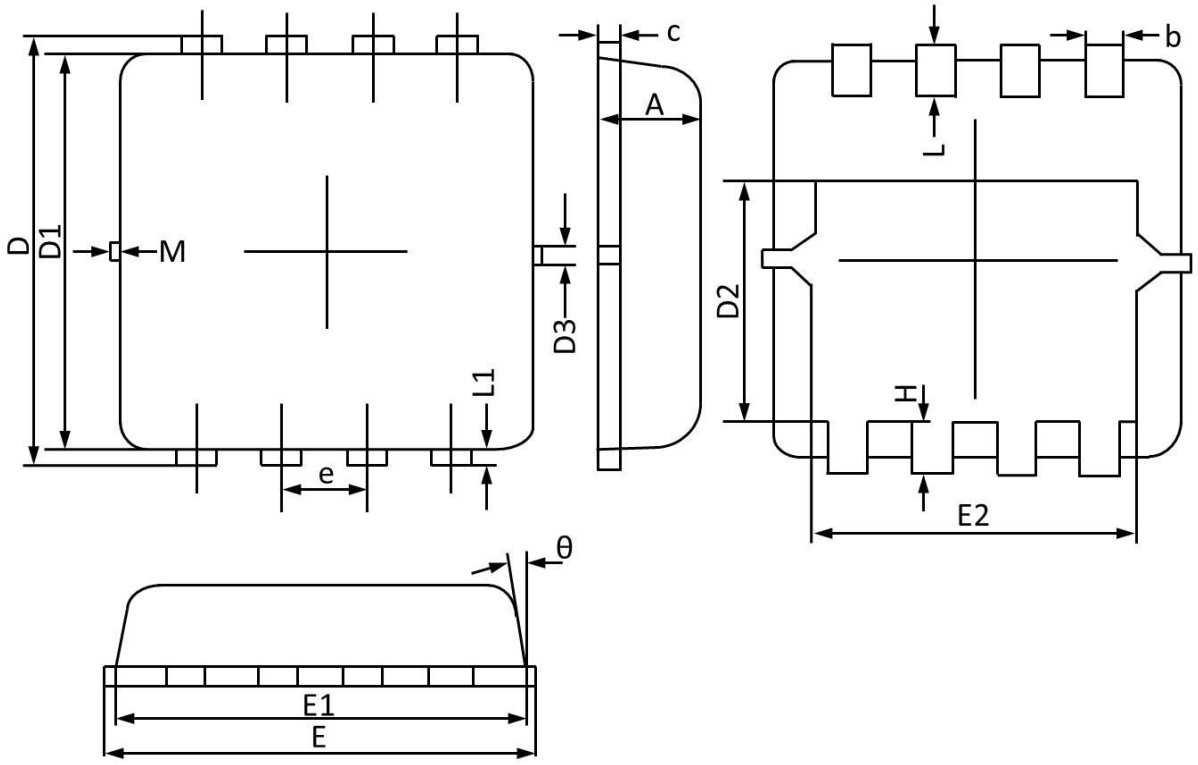
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



PDFN3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	